

Fig. 5. Calculated reflectivity spectra and thickness deviation dependency of the five-period a-Si/a-Si DBR as a function of wavelength.

Figure 6 (a) shows a digital photographic image of the deposited a-Si/a-Si DBR shaped as the media mark of an institute. Any size or any feature of a structure can be fabricated by a simple lift-off process for the realization of a highly reflective broadband DBR suitable for various optoelectronic devices. As shown in Fig. 6 (b), the relative reflectivity of the patterned structure at 1550 nm was plainly higher than that of a normal Si (100) substrate and the superiority of the tolerant a-Si/a-Si DBR and its fabrication process are clearly evident.

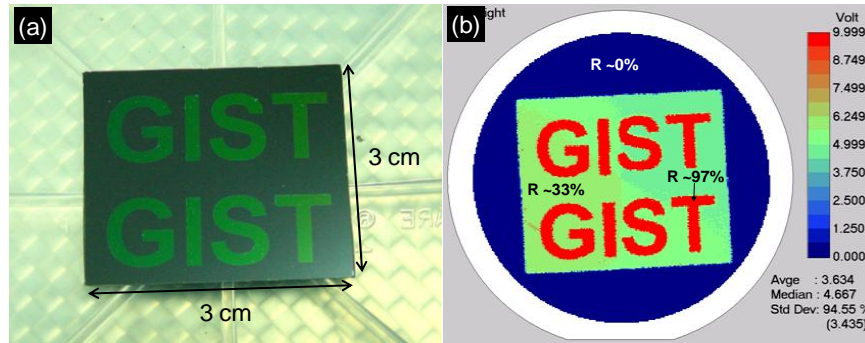


Fig. 6. (a) Photographic image of 'GIST'-patterned a-Si/a-Si DBR on Si substrate. (b) Relative reflectance mapping image of 'GIST'-patterned a-Si/a-Si DBR on Si substrate.

4. Conclusion

In summary, we proposed a novel class of DBRs based the OAD of a-Si. The reflective characteristics were investigated both theoretically and experimentally. Highly tolerant and highly reflective broadband a-Si/a-Si DBRs were demonstrated successfully for the first time. A broadband stop band ($\Delta\lambda/\lambda = 33.7\%$, $R > 99\%$) with only a five-period a-Si/a-Si DBR was achieved experimentally. The size-, feature- and substrate-independent method to realize highly tolerant and broadband DBRs will provide an interesting new pathway that opens future practical applications such as resonant-cavity-light-emitting-diodes or vertical-cavity-surface-emitting-lasers or solar cells. In an addition, oblique-angle deposition is promising for the growth of homogeneous highly reflective DBR structures with a very high refractive index contrast.

Acknowledgments

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